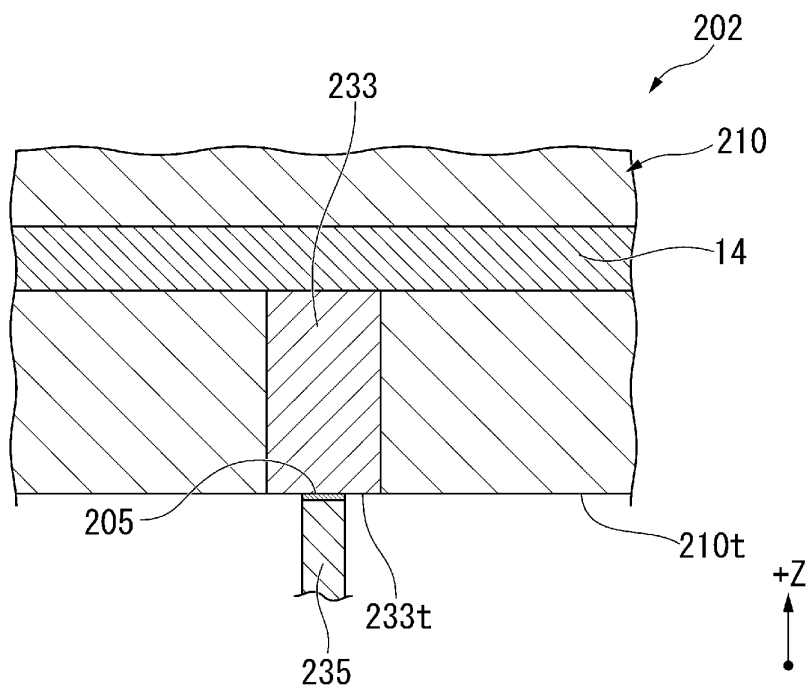


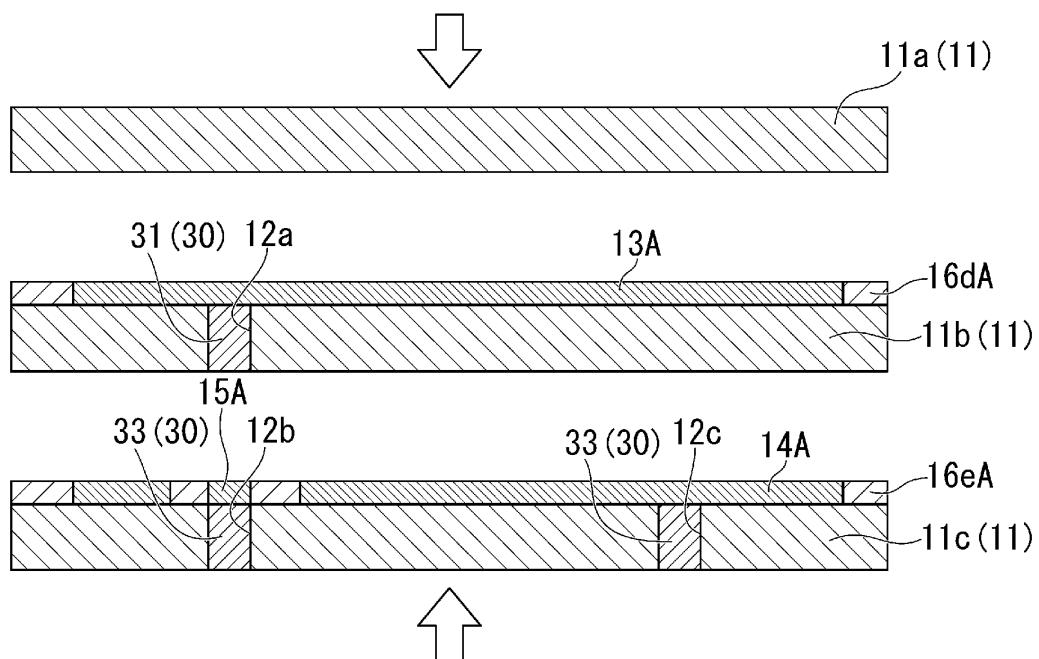


Figure 2 is a cross-sectional view of a semiconductor device 2. The device includes a substrate 10 with a top layer 10t, a middle layer 11b, and a bottom layer 11c. A central region 33 is defined by a vertical wall 33d. Within this region, there is a structure 35 consisting of layers 33a, 33b, 33c, and 33d. A contact 5 is located at the bottom of the central region 33. A +Z axis is indicated by an arrow pointing upwards.

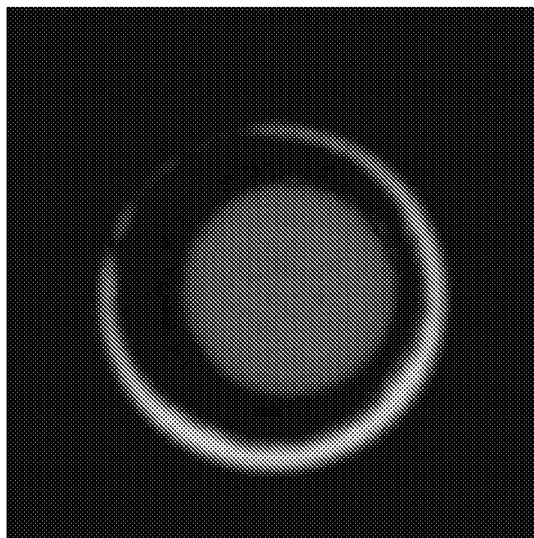
[図4]



[図5]



[図6]



[図7]

